

Surface Mount Glass Passivated Fast Recovery Rectifier

SMAF(eSGB)			Features								
				 ROHS compliant Glass passivated chip High forward surge capability Meet MSL level 1, per J-STD-020 LF maximum peak of 250 °C Solder dip 260 °C / 40S Component in accordance to ROHS 2002/95/EC and WEEE 2002/96/WC UL recognition, file number E342874 							
Primary characteristics			Applications								
I _{F(AV)}		2A	Ideal	for ac-	-to-dc	bridge	e full w	ave re	ectifica	ation s	uck as
V _{RRM}	50V t	o 1000V	SMPS	S, hom	ne app	lianes	, offic	e equi	pmen	t, indus	srial
I _{FSM}	6	60A	SMPS, home applianes, office equipment, indusrial automation applicatios								
I _{RM}		5uA	1								
V _{FM} at I _F =2A		.3V	Mechanical data								
T_J max.		.3v 60 °C	SMAF(eSGB)								
Maximum rating (Ta	a=25°C เ	inless othe	 Po Mo Re 	comm	As ma Torqu endec	irked. ue:100	cm-kg	(8.8 in		bs)ma ches-lb	
Parameter			Sym	SVm SMAF(eSGB)				Unit			
			Sym	L2F1	L2F2	L2F3	L2F4	L2F5	L2F6	L2F7	Om
Max. repetitive peak reverse voltage						1		800			
	e voltage		Vrrm	50	100	200	400	600		1000	V
Max. RMS reverse voltage	e voltage		V _{RRM} V _{RMS}	35	100 70	200 140	280	600 420	560	700	V V
Max. RMS reverse voltage Max. DC blocking voltage									560 800		
Max. RMS reverse voltage Max. DC blocking voltage Max. average forward curre	nt		V _{RMS}	35	70	140	280	420		700	V
Max. RMS reverse voltage Max. DC blocking voltage Max. average forward curre Non-repetitive peak forward	nt surge curr	ent	V _{RMS} V _{DC}	35	70	140	280 400	420		700	V V
Max. RMS reverse voltage Max. DC blocking voltage Max. average forward curre Non-repetitive peak forward 8.3ms single half-sine-wave	nt surge curr		Vrms Vdc If(av) Ifsm	35	70	140 200	280 400 2 60	420 600		700	V V A A
Max. RMS reverse voltage Max. DC blocking voltage Max. average forward curre Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward	nt surge curr voltage dr	op per diode	VRMS VDC IF(AV)	35	70	140 200	280 400 2 60 1.3 (2A)	420 600		700	V V A
Max. RMS reverse voltage Max. DC blocking voltage Max. average forward curre Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse	nt surge curr voltage dr current	op per diode Ta=25 °C	Vrms Vdc If(av) Ifsm	35	70	140 200	280 400 2 60 .3 (2A) 5	420 600		700	V V A A
Max. RMS reverse voltage Max. DC blocking voltage Max. average forward curre Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltage	nt surge curr voltage dr current	op per diode	V _{RMS} V _{DC} I _{F(AV)} I _{FSM} V _{FM} I _{RM}	35	70	140 200	280 400 2 60 1.3 (2A) 5 50	420 600		700	V V Α Λ V μΑ
Max. RMS reverse voltage Max. DC blocking voltage Max. average forward curre Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltage Operating junction temperat	nt surge curr voltage dr current	op per diode Ta=25 °C	VRMS VDC IF(AV) IFSM VFM IRM TJ	35	70	140 200 1 -5	280 400 2 60 1.3 (2A) 5 50 50 5 ~ +15	420 600		700	V V Α Α V μΑ °C
Max. RMS reverse voltage Max. DC blocking voltage Max. average forward curre Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltage Operating junction temperat Storage temperature	nt surge curr voltage dr current e ture	op per diode Ta=25 °C	VRMS VDC IF(AV) IFSM VFM IRM TJ TSTG	35	70 100	140 200 1 -5 -5	280 400 2 60 1.3 (2A) 5 50	420 600	800	700	V V A A V μA °C °C
Max. RMS reverse voltage Max. DC blocking voltage Max. average forward curre Non-repetitive peak forward 8.3ms single half-sine-wave Max. instantaneous forward Max. instantaneous reverse at rated DC blocking voltage Operating junction temperat	nt surge curr voltage dr current e ture	op per diode Ta=25 °C	VRMS VDC IF(AV) IFSM VFM IRM TJ	35	70	140 200 1 -5 -5	280 400 2 60 1.3 (2A) 5 50 50 5 ~ +15	420 600	800	700	V V Α Α V μΑ °C

Notes:

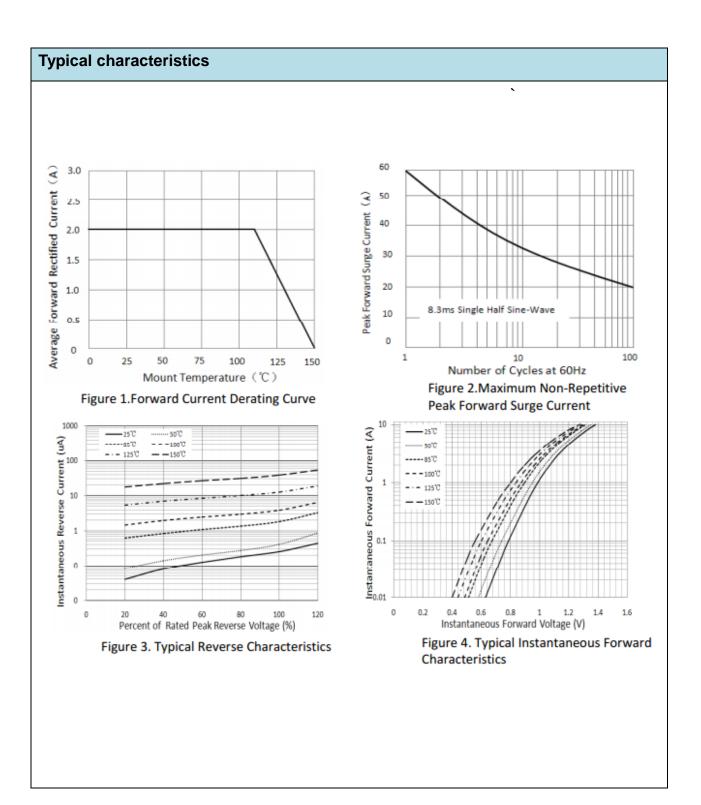
1 The thermal resistance from junction to mount,mounted on P.C.B with 8x8mm copper pads,2 OZ,FR4 PCB

2. Measured at 1 MHz and Applied Reverse Voltage of 4.0 V D.C



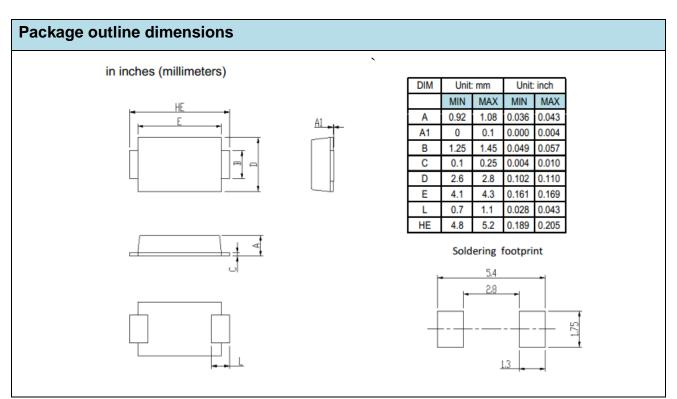
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Ordering information (Example)								
PREFERRED	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE				
L2F7								





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